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Feasibility of Fabrication of Heteroepitaxial $Ge_x Si_{1-x}$ /Si(111) structure by Pulsed Nd: YAG Laser
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<u>Abstract:</u> Heteroepitaxial Ge _x Si _{1-x} alloy layers have been formed by 10 ms and 300 μ s laser pulse
induced mixing of pure germanium films and Si(111) substrates where Ge films of thickness (500-1250) Å are thermally evaporated onto Si(111) under vacuum pressure \sim 10^{-5} Torr. The near surface of the sample then undergoes rapid melting and regrowth processes during each pulse from a free running Nd; YAG laser. The alloy layers are (4.6-6.5) µm thick and have a Ge fraction of x = 6-8.2%.
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